

**Description**

The WPEXXCT23BL is a bi-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast re-sponse time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The WPEXXCT23BL complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

**Features**

- 300W peak pulse power (8/20µs)
- Protects two bi-directional lines
- Ultra low leakage: nA level
- Operating voltage: 3.3V, 5V, 12V, 15V, 24V, 32V, 36V
- Low clamping voltage
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±30kV
    - Contact discharge: ±30kV
- RoHS Compliant

**Mechanical Characteristics**

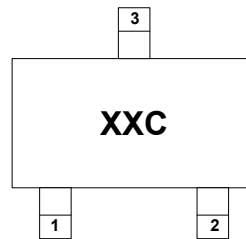
- Package: SOT-23
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

**Applications**

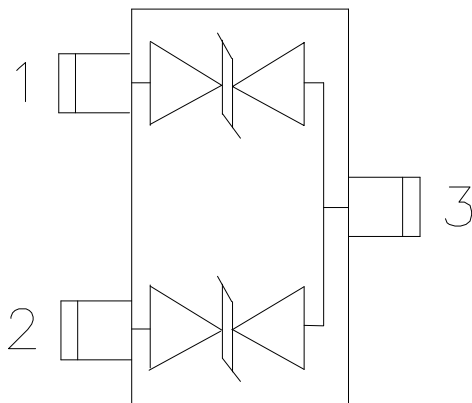
- Cellular Handsets and Accessories
- Notebooks and Handhelds
- Portable Instrumentation
- Set Top Box
- Industrial Controls
- Server and Desktop PC

**Marking Information**

XXC = Device Marking



**Dimensions and Pin Configuration**



Circuit and Pin Schematic

**Ordering Information**

Part Number	Packaging	Reel Size
WPEXXCT23BL	3000/Tape & Reel	7 inch

**Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	300	W
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV
ESD per IEC 61000-4-2 (Contact)		±30	
Operating Temperature Range	T <sub>J</sub>	-55 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)**

<b>WPE03CT23BL</b>						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V <sub>RWM</sub>			3.3	V	
Breakdown Voltage	V <sub>BR</sub>	3.8			V	I <sub>T</sub> = 1mA
Reverse Leakage Current	I <sub>R</sub>			1.0	μA	V <sub>RWM</sub> = 3.3V
Clamping Voltage	V <sub>C</sub>			6	V	I <sub>PP</sub> = 1A (8 x 20μs pulse)
Clamping Voltage	V <sub>C</sub>			12	V	I <sub>PP</sub> = 25A (8 x 20μs pulse)
Peak Pulse Current	I <sub>PP</sub>			25	A	t <sub>p</sub> = 8/20μs
Junction Capacitance	C <sub>J</sub>			100	pF	V <sub>R</sub> = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3

<b>WPE05CT23BL</b>						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V <sub>RWM</sub>			5	V	
Breakdown Voltage	V <sub>BR</sub>	6			V	I <sub>T</sub> = 1mA
Reverse Leakage Current	I <sub>R</sub>			1.0	μA	V <sub>RWM</sub> = 5V
Clamping Voltage	V <sub>C</sub>			8	V	I <sub>PP</sub> = 1A (8 x 20μs pulse)
Clamping Voltage	V <sub>C</sub>			15	V	I <sub>PP</sub> = 20A (8 x 20μs pulse)
Peak Pulse Current	I <sub>PP</sub>			20	A	t <sub>p</sub> = 8/20μs
Junction Capacitance	C <sub>J</sub>			80	pF	V <sub>R</sub> = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3

<b>WPE12CT23BL</b>						
<b>Parameter</b>	<b>Symbol</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>	<b>Test Condition</b>
Reverse Working Voltage	VRWM			12	V	
Breakdown Voltage	VBR	13.3			V	IT = 1mA
Reverse Leakage Current	IR			0.5	µA	VRWM = 12V
Clamping Voltage	VC			18	V	I <sub>PP</sub> = 1A (8 x 20µs pulse)
Clamping Voltage	VC			25	V	I <sub>PP</sub> = 12A (8 x 20µs pulse)
Peak Pulse Current	I <sub>PP</sub>			12	A	t <sub>p</sub> = 8/20µs
Junction Capacitance	C <sub>J</sub>			50	pF	VR = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3

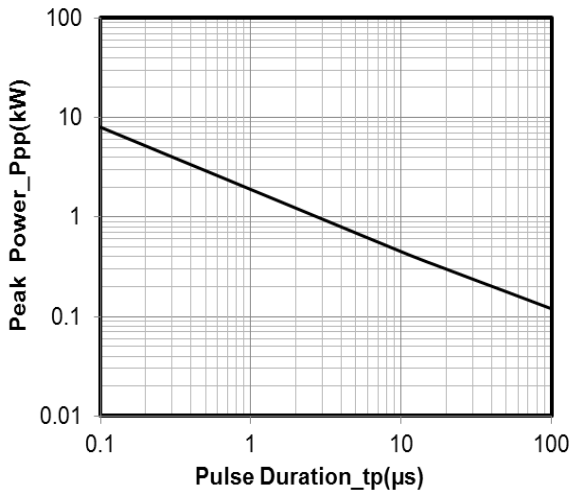
<b>WPE15CT23BL</b>						
<b>Parameter</b>	<b>Symbol</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>	<b>Test Condition</b>
Reverse Working Voltage	VRWM			15	V	
Breakdown Voltage	VBR	16.7			V	IT = 1mA
Reverse Leakage Current	IR			0.5	µA	VRWM = 15V
Clamping Voltage	VC			20	V	I <sub>PP</sub> = 1A (8 x 20µs pulse)
Clamping Voltage	VC			37.5	V	I <sub>PP</sub> = 8A (8 x 20µs pulse)
Peak Pulse Current	I <sub>PP</sub>			8	A	t <sub>p</sub> = 8/20µs
Junction Capacitance	C <sub>J</sub>			40	pF	VR = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3

<b>WPE24CT23BL</b>						
<b>Parameter</b>	<b>Symbol</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>	<b>Test Condition</b>
Reverse Working Voltage	VRWM			24	V	
Breakdown Voltage	VBR	27			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 24V
Clamping Voltage	VC			40	V	I <sub>PP</sub> = 1A (8 x 20μs pulse)
Clamping Voltage	VC			60	V	I <sub>PP</sub> = 5A (8 x 20μs pulse)
Peak Pulse Current	I <sub>PP</sub>			5	A	t <sub>p</sub> = 8/20μs
Junction Capacitance	C <sub>J</sub>		15	30	pF	VR = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3

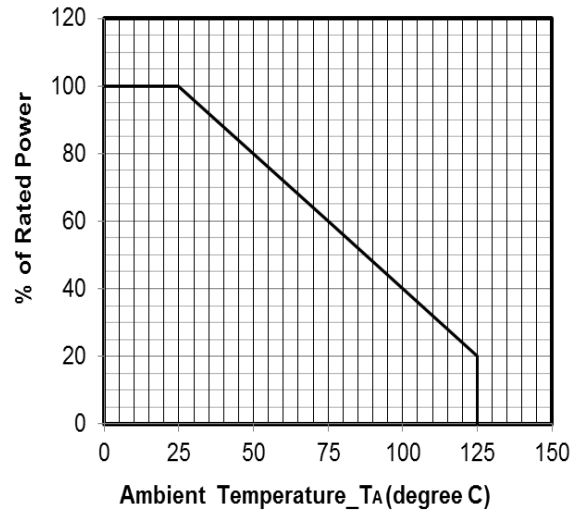
<b>WPE32CT23BL</b>						
<b>Parameter</b>	<b>Symbol</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>	<b>Test Condition</b>
Reverse Working Voltage	VRWM			32	V	
Breakdown Voltage	VBR	35.6			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 36V
Clamping Voltage	VC			45	V	I <sub>PP</sub> = 1A (8 x 20μs pulse)
Clamping Voltage	VC			67	V	I <sub>PP</sub> = 4.5A (8 x 20μs pulse)
Peak Pulse Current	I <sub>PP</sub>			4	A	t <sub>p</sub> = 8/20μs
Junction Capacitance	C <sub>J</sub>		15	25	pF	VR = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3

<b>WPE36CT23BL</b>						
<b>Parameter</b>	<b>Symbol</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Unit</b>	<b>Test Condition</b>
Reverse Working Voltage	VRWM			36	V	
Breakdown Voltage	VBR	38			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 36V
Clamping Voltage	VC			50	V	I <sub>PP</sub> = 1A (8 x 20μs pulse)
Clamping Voltage	VC			75	V	I <sub>PP</sub> = 4A (8 x 20μs pulse)
Peak Pulse Current	I <sub>PP</sub>			4	A	t <sub>p</sub> = 8/20μs
Junction Capacitance	C <sub>J</sub>		12	20	pF	VR = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3

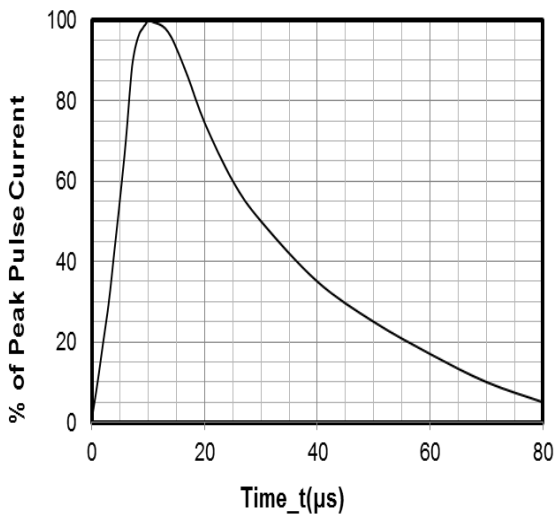
**Typical Performance Characteristics (T<sub>A</sub>=25°C unless otherwise Specified)**



**Peak Pulse Power vs. Pulse Time**

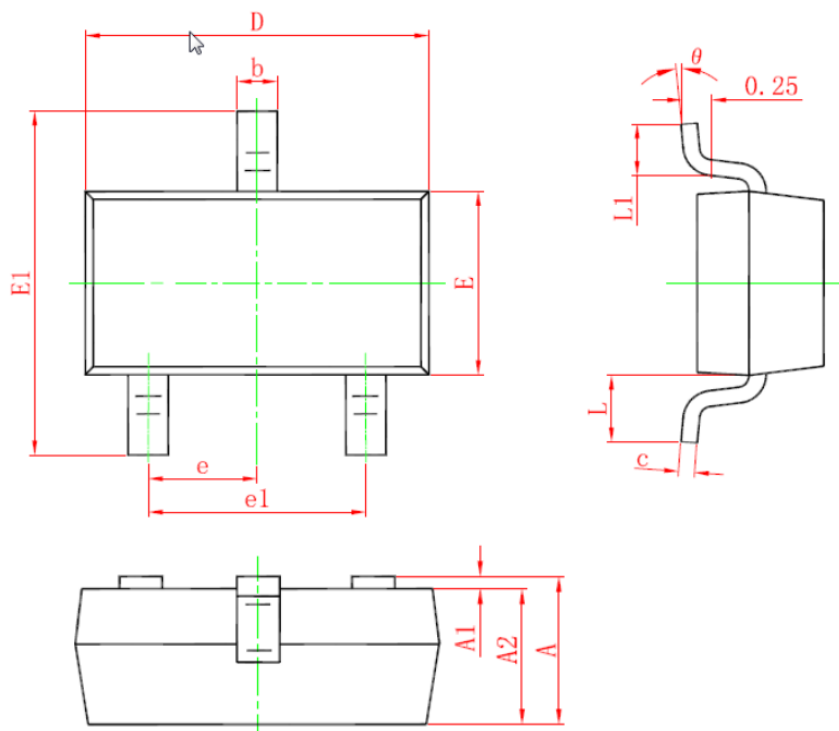


**Power Derating Curve**



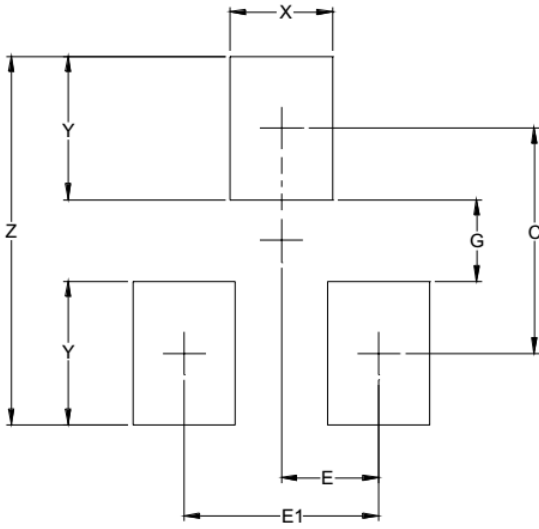
**8 X 20μs Pulse Waveform**

**SOT-23 Package Outline Drawing**



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	--	1.15	0.035	--	0.045
A1	0.00	--	0.10	0.000	--	0.004
A2	0.90	--	1.05	0.035	--	0.041
b	0.30	--	0.50	0.012	--	0.020
c	0.08	--	0.15	0.003	--	0.006
D	2.80	--	3.00	0.110	--	0.118
E	1.20	--	1.40	0.047	--	0.055
E1	2.25	--	2.25	0.089		0.100
e	0.95TYP			0.037TYP		
e1	1.80	--	2.00	0.071	--	0.079
L	0.55REF			0.022REF		
L1	0.30	--	0.50	0.012	--	0.020
θ	0°	--	8°	0°	--	8°

**Suggested Land Pattern**



SYM	DIMENSIONS	
	INCHES	MILLIMETERS
C	.087	2.20
E	.037	0.95
E1	.075	1.90
G	.031	0.80
X	.039	1.00
Y	.055	1.40
Z	.141	3.60

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